2SC5552

Silicon NPN triple diffusion mesa type

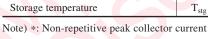
For horizontal deflection output

■ Features

- High breakdown voltage, and high reliability through the use of a glass passivation layer
- High-speed switching
- Wide safe operation area

■ Absolute Maximum Ratings $T_C = 25^{\circ}C$

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open) V _{CBO}	1700	V	
Collector-emitter voltage (E-B short)	V _{CES}	1700	V	
Collector-emitter voltage (Base open) V _{CEO}	600	V	
Emitter-base voltage (Collector open) V _{EBO}	7	V	
Base current	I_{B}	8	A	
Collector current	I_{C}	16	A	
Peak collector current *	I_{CP}	30	A	
Collector power dissipation	$P_{\rm C}$	65	W	
$T_a = 25^{\circ}C$		3.5	5 xe	
Junction temperature	T_{j}	150	°C	
Storage temperature	$T_{\rm stg}$	-55 to +150	°C	



Unit: mm 15.5±0.5 (4.0) (2.0±0.2 1.1±0.1 0.7±0.1 1: Base 2: Collector 3: Emitter EIAJ: SC-94 TOP-3E-Al Package

■ Electrical Characteristics $T_C = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base cutoff current (Emitter open)	I_{CBO}	$V_{CB} = 1000 \text{ V}, I_E = 0$			50	μΑ
"Silion		$V_{CB} = 1700 \text{ V}, I_{E} = 0$			1	mA
Emitter-base cutoff current (Collector open)	I_{EBO}	$V_{EB} = 7 \text{ V}, I_{C} = 0$			50	μΑ
Forward current transfer ratio	h _{FE}	$V_{CE} = 5 \text{ V}, I_{C} = 8 \text{ A}$	6		12	_
Collector-emitter saturation voltage	V _{CE(sat)}	$I_C = 8 \text{ A}, I_B = 2 \text{ A}$			3	V
Base-emitter saturation voltage	V _{BE(sat)}	$I_C = 8 \text{ A}, I_B = 2 \text{ A}$			1.5	V
Transition frequency	f_T	$V_{CE} = 10 \text{ V}, I_{C} = 0.1 \text{ A}, f = 0.5 \text{ MHz}$		3		MHz
Storage time	t _{stg}	I _C = 8 A, Resistance loaded			3.0	μs
Fall time	t _f	$I_{B1} = 2 A, I_{B2} = -4 A$			0.2	μs

 $Note)\ Measuring\ methods\ are\ based\ on\ JAPANESE\ INDUSTRIAL\ STANDARD\ JIS\ C\ 7030\ measuring\ methods\ for\ transistors.$

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